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SESSION 1: Sensors

2010 Mar 23, 9:10 – 10:30

Co-Chairs: Emilio Lora-Tamayo, *Universitat Autonoma de Barcelona, Spain*
Yoshio Mita, *The University of Tokyo, Japan*

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[1] *Infineon Technologies Romania, Romania,* [2] *Infineon Technologies AG, Germany,*
[3] *Vienna University of Technology, Austria*

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[1]*The University of Edinburgh, UK,* [2] *Newcastle University, UK*

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[3]*The University of Dundee, Scotland*

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[1]*CEA LETI-Minatec France,* [2]*ST-Microelectronics, France,* [3]*Universita degli Studi di Modena e Reggio Emili,a Italy*

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Co-Chairs: Jurriaan Schmitz, *University of Twente, Netherlands*
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Co-Chairs: Satoshi Habu, *Agilent Technologies, Inc., Japan*
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[1]*IMEC, Belgium,* [2]*K.U.Leuven, Belgium,* [3]*Qualcomm CDMA Technologies, Belgium*

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[1]*Fujitsu Microelectronics Japan,* [2]*Fujitsu VLSI, Japan*

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[3]*EPCOS, Netherlands*

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Co-Chairs: Larg H. Wieland*, PDF Solutions, USA*
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[1]*STMicroelectronics, France,* [2]*IBM France*

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[1]*Kobe University, Japan,* [2]*MIRAI-Selete, Japan*